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TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $L^2-\pi$ -MOSV)

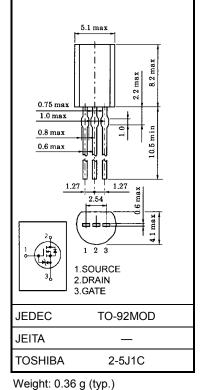
# 2SK2961

Relay Drive, Motor Drive and DC–DC Converter Application

- Low drain-source ON resistance : RDS (ON) = 0.2  $\Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 2.0 \text{ S (typ.)}$
- Low leakage current  $: I_{DSS} = 100 \ \mu A \ (V_{DS} = 60 \ V)$
- Enhancement-mode :  $V_{th} = 0.8 \sim 2.0 V (V_{DS} = 10 V, I_D = 1 mA)$

#### Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	60	V	
Drain-gate voltage (R	<sub>GS</sub> = 20 kΩ)	V <sub>DGR</sub>	60	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC (Note 1)	۱ <sub>D</sub>	2.0	А	
	Pulse (Note 1)	I <sub>DP</sub>	6.0	A	
Drain power dissipation	ı	PD	0.9	W	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	



### Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R <sub>th (ch−a)</sub>	138	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

This transistor is an electrostatic sensitive device. Please handle with caution. Unit: mm

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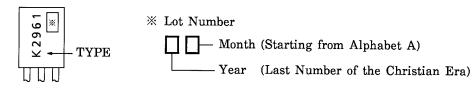
#### Electrical Characteristics (Ta = 25°C)

Charao	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cu	ırrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0 V		—	±10	μA	
Drain cut-off cu	rrent	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	-	_	100	μA	
Drain-source br	eakdown voltage	V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	60	_		V	
Gate threshold v	voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	0.8	_	2.0	V	
Drain-source ON resistance		R <sub>DS (ON)</sub>	V <sub>GS</sub> = 4 V, I <sub>D</sub> = 1.0 A		0.26	0.38	Ω	
			V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.0 A	_	0.20	0.27		
Forward transfe	r admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 A	1.0	2.0	—	S	
Input capacitance		Ciss		_	170		pF	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	25	_		
Output capacitance		C <sub>oss</sub>			75	_		
Switching time	Rise time	tr	$v_{GS} \xrightarrow{10V}_{0V} \prod_{\substack{I_D = 1A \\ V \cup U \cup V \cup U}} v_{OUT}$	_	10	_		
	Turn-on time	t <sub>on</sub>		_	15	_	ns	
	Fall time	t <sub>f</sub>		_	50	_		
	Turn-off time	t <sub>off</sub>	Duty $\leq 1\%$ , t <sub>w</sub> =10µs	_	170	_		
Total gate charge (gate-source plus gate-drain)		Qg		_	5.8	_		
Gate-source charge		Q <sub>gs</sub>	V <sub>DD</sub> ≈ 48 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2 A		4.1	_	nC	
Gate-drain ("miller") Charge		Q <sub>gd</sub>			1.7	_		

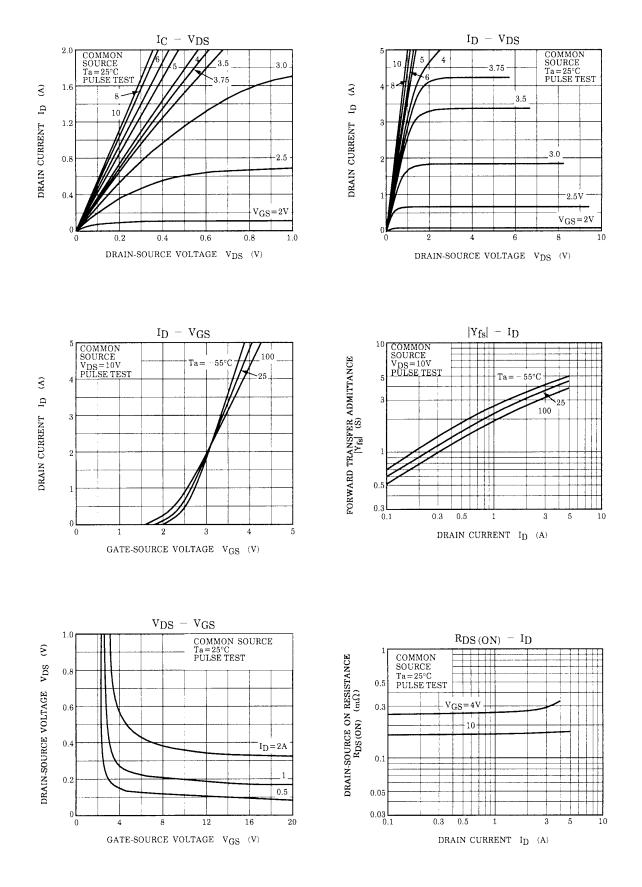
#### Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	—	_	_	2.0	А
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	—	_	_	6.0	А
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 2 A, V <sub>GS</sub> = 0 V	_	—	-1.5	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 2 A, V <sub>GS</sub> = 0 V, dI <sub>DR</sub> / dt = 50 A / µs	_	45	_	ns
Reverse recovery charge	Q <sub>rr</sub>	$1DR = 2A$ , $VGS = 0V$ , $0DR / 01 = 50A / \mu s$		40.5		nC

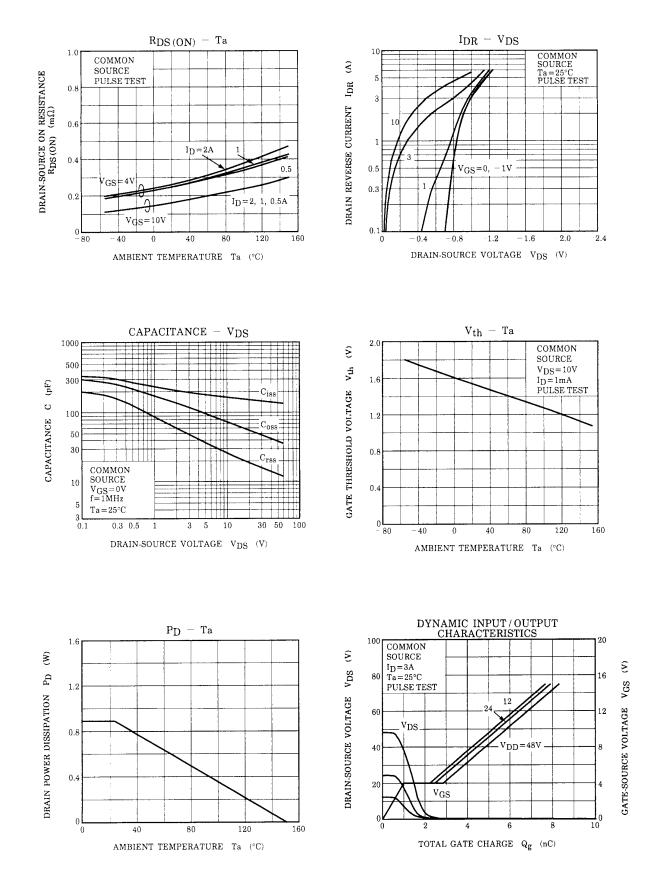
#### Marking

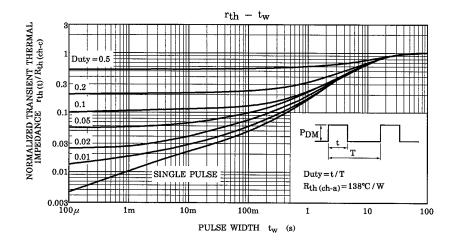


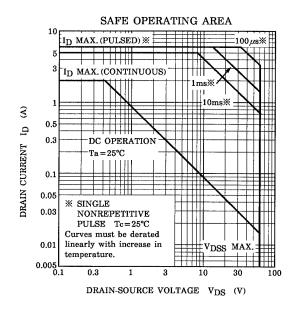
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